

9097250 TOSHIBA (DISCRETE/OPTO)

99D 16890 DT-39-11



SEMICONDUCTOR

TECHNICAL DATA

TOSHIBA FIELD EFFECT TRANSISTOR

YTF823

SILICON N CHANNEL MOS TYPE

(π-MOS II)

HIGH SPEED, HIGH CURRENT SWITCHING APPLICATIONS.

CHOPPER REGULATOR, DC-DC CONVERTER AND MOTOR
DRIVE APPLICATIONS.

FEATURES:

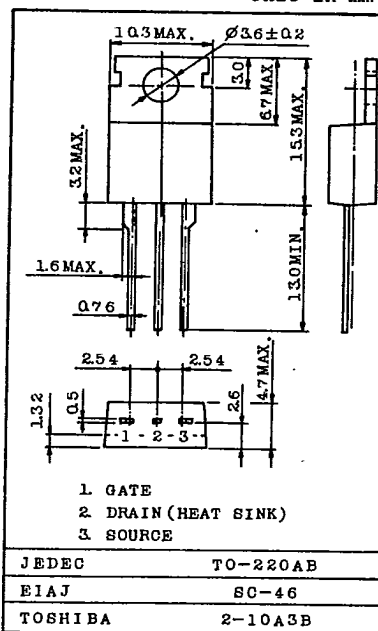
- Low Drain-Source ON Resistance : $R_{DS(ON)} = 3.0\Omega$ (Typ.)
- High Forward Transfer Admittance : $|Y_{fs}| = 1.75S$ (Typ.)
- Low Leakage Current : $I_{GSS} = \pm 500nA$ (Max.) @ $V_{GS} = \pm 20V$
 $I_{DSS} = 250\mu A$ (Max.) @ $V_{DS} = 450V$
- Enhancement-Mode : $V_{th} = 2.0 \sim 4.0V$ @ $V_{DS} = V_{GS}$, $I_D = 250\mu A$

MAXIMUM RATINGS ($T_a = 25^\circ C$)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Drain-Source Voltage	V_{DSX}	450	V
Drain-Gate Voltage ($R_{GS} = 1M\Omega$)	V_{DGR}	450	V
Gate-Source Voltage	V_{GSS}	± 20	V
Drain Current	DC ($T_c = 25^\circ C$)	I_D	2
	DC ($T_c = 100^\circ C$)	I_D	1
	Pulse	I_{DP}	8
Inductive Current (Clamped)	I_{LP}	8	A
Drain Power Dissipation ($T_c = 25^\circ C$)	P_D	40	W
Channel Temperature	T_{ch}	150	$^\circ C$
Storage Temperature Range	T_{stg}	$-55 \sim 150$	$^\circ C$

INDUSTRIAL APPLICATIONS

Unit in mm



Weight : 1.9g

THERMAL CHARACTERISTICS

CHARACTERISTIC	SYMBOL	MAX.	UNIT
Thermal Resistance, Junction to Case	$R_{th(j-c)}$	3.12	$^\circ C/W$
Thermal Resistance, Junction to Ambient	$R_{th(j-a)}$	80	$^\circ C/W$
Maximum Lead Temperature for Soldering Purposes (1.6mm from case for 10 seconds)	T_L	300	$^\circ C$

TOSHIBA CORPORATION

GT1A2

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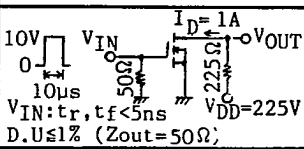


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ELECTRICAL CHARACTERISTICS (Ta=25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Gate Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	± 500	nA
Drain Cut-off Current	I_{DSS}	$V_{DS}=450V, V_{GS}=0V, T_c=25^\circ C$	-	-	250	μA
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$I_D=250\mu A, V_{GS}=0V$	450	-	-	V
Gate Threshold Voltage	V_{th}	$V_{DS}=V_{GS}, I_D=250\mu A$	2.0	-	4.0	V
Forward Transfer Admittance	$ Y_{fs} $	$V_{DS}=10V, I_D=1A$	1.0	1.75	-	S
On-State Drain Current	$I_{D(ON)}$	$V_{DS}=10V, V_{GS}=10V$	2.0	-	-	A
Drain-Source ON Resistance	$R_{DS(ON)}$	$I_D=1A, V_{GS}=10V$	-	3.0	4.0	Ω
Drain-Source ON Voltage	$V_{DS(ON)}$	$I_D=2A, V_{GS}=10V$	-	6.6	9.4	V
Input Capacitance	C_{iss}	$V_{DS}=25V, V_{GS}=0V, f=1MHz$	-	300	400	pF
Reverse Transfer Capacitance	C_{rss}		-	30	40	pF
Output Capacitance	C_{oss}		-	120	150	pF
Switching Time	Rise Time		-	25	50	ns
	Turn-on Time		-	55	110	ns
	Fall Time		-	15	30	ns
	Turn-off Time		-	45	90	ns
Total Gate Charge (Gate-Source Plus Gate-Drain)	Q_g	$V_{GS}=10V, I_D=3A,$	-	11	15	nC
Gate Source Charge	Q_{gs}	$V_{DS}=360V$	-	5	-	nC
Gate-Drain ("Miller") Charge	Q_{gd}		-	6	-	nC

SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (Ta=25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Continuous Source Current	I_S	—	-	-	2	A
Pulse Source Current	I_{Sp}	—	-	-	8	A
Diode Forward Voltage	V_{SD}	$I_S=2A, V_{GS}=0V, T_c=25^\circ C$	-	-	1.5	V
Reverse Recovery Time	t_{rr}	$T_j=150^\circ C, I_F=2.5A,$	-	600	-	ns
Reverse Recovered Charge	Q_{rr}	$dI_F/dt=100A/\mu s$	-	3.5	-	μC

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